

SKM800GA126D



SEMITRANS® 4

Trench IGBT Modules

SKM800GA126D

Features

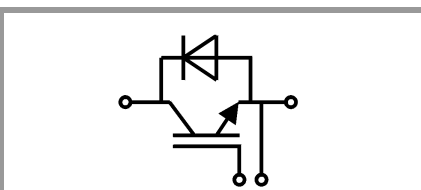
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$
- UL recognized, file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders

Remarks

- $I_{DC} \leq 500A$ limited by terminals



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Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
IGBT			
V_{CES}	$T_j = 25\text{ °C}$	1200	V
I_C	$T_j = 150\text{ °C}$	$T_c = 25\text{ °C}$	910
		$T_c = 80\text{ °C}$	635
I_{Cnom}		600	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	1200	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 600\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 125\text{ °C}$	10
			μs
T_j		-40 ... 150	°C
Inverse diode			
I_F	$T_j = 150\text{ °C}$	$T_c = 25\text{ °C}$	703
		$T_c = 80\text{ °C}$	480
I_{Fnom}		600	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	1200	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25\text{ °C}$	4680	A
T_j		-40 ... 150	°C
Module			
$I_{t(RMS)}$		500	A
T_{stg}		-40 ... 125	°C
V_{isol}	AC sinus 50 Hz, $t = 1\text{ min}$	4000	V

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 600\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ °C}$	1.70	2.10	V
		$T_j = 125\text{ °C}$	2.00	2.48	V
V_{CE0}	chipelevel	$T_j = 25\text{ °C}$	1	1.2	V
		$T_j = 125\text{ °C}$	0.9	1.1	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ °C}$	1.17	1.50	mΩ
		$T_j = 125\text{ °C}$	1.83	2.3	mΩ
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 24\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25\text{ °C}$		5	mA
		$T_j = 125\text{ °C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	43.1		nF
C_{oes}		$f = 1\text{ MHz}$	2.25		nF
C_{res}		$f = 1\text{ MHz}$	1.95		nF
Q_G	$V_{GE} = -8\text{ V} \dots +20\text{ V}$		5200		nC
R_{Gint}	$T_j = 25\text{ °C}$		1.3		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$ $I_C = 600\text{ A}$	$T_j = 125\text{ °C}$	220		ns
t_r	$V_{GE} = +15/-15\text{ V}$	$T_j = 125\text{ °C}$	100		ns
E_{on}	$R_{Gon} = 3\text{ Ω}$	$T_j = 125\text{ °C}$	65		mJ
$t_{d(off)}$	$R_{Goff} = 3\text{ Ω}$	$T_j = 125\text{ °C}$	860		ns
t_f		$T_j = 125\text{ °C}$	135		ns
E_{off}		$T_j = 125\text{ °C}$	95		mJ
$R_{th(j-c)}$	per IGBT			0.042	K/W



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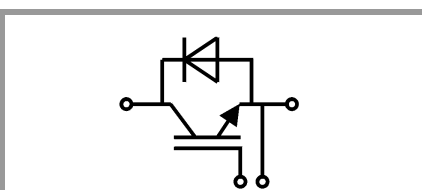
Typical Applications*

- AC inverter drives
- UPS
- Electronic welders

Remarks

- $I_{DC} \leq 500A$ limited by terminals

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 600 A$ $V_{GE} = 0 V$ chipllevel	$T_j = 25 \text{ }^\circ C$		1.60	1.80	V
		$T_j = 125 \text{ }^\circ C$		1.60	1.80	V
V_{F0}	chipllevel	$T_j = 25 \text{ }^\circ C$		1	1.1	V
		$T_j = 125 \text{ }^\circ C$		0.8	0.9	V
r_F	chipllevel	$T_j = 25 \text{ }^\circ C$		1.00	1.17	m Ω
		$T_j = 125 \text{ }^\circ C$		1.33	1.50	m Ω
I_{RRM}	$I_F = 600 A$	$T_j = 125 \text{ }^\circ C$		540		A
Q_{rr}	$di/dt_{off} = 6000 A/\mu s$	$T_j = 125 \text{ }^\circ C$		125		μC
E_{rr}	$V_{GE} = -15 V$ $V_{CC} = 600 V$	$T_j = 125 \text{ }^\circ C$		59		mJ
$R_{th(j-c)}$	per diode				0.09	K/W
Module						
L_{CE}				15		nH
$R_{CC'+EE'}$	terminal-chip	$T_C = 25 \text{ }^\circ C$		0.18		m Ω
		$T_C = 125 \text{ }^\circ C$		0.22		m Ω
$R_{th(c-s)}$	per module			0.02	0.038	K/W
M_s	to heat sink M6			3	5	Nm
M_t	to terminals	M6		2.5	5	Nm
		M4		1.1	2	Nm
w					330	g



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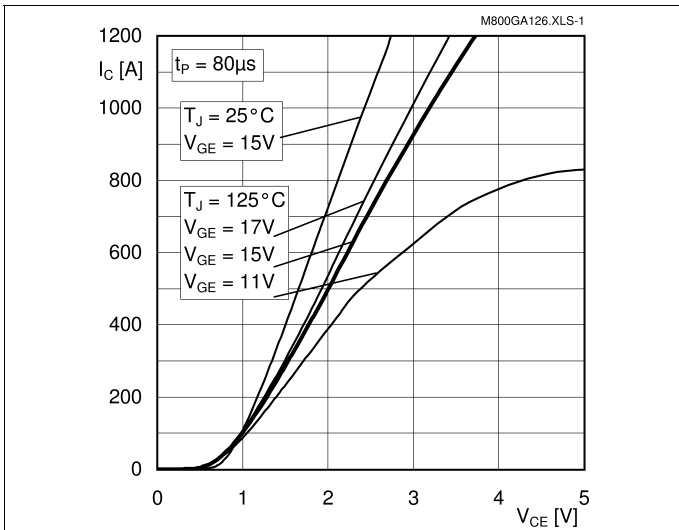


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

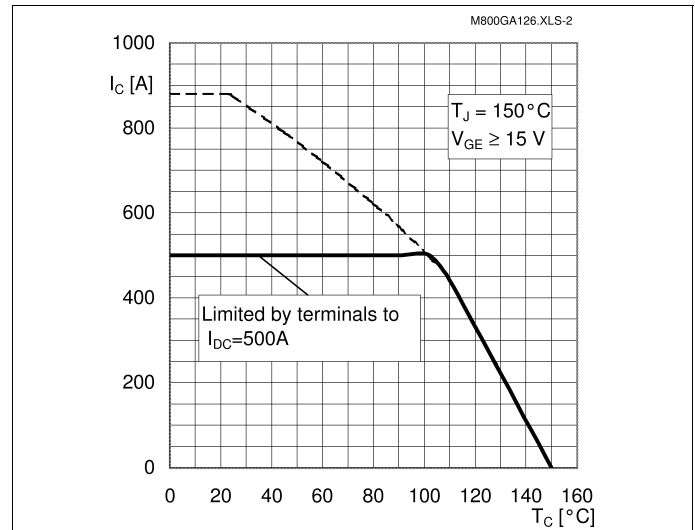


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

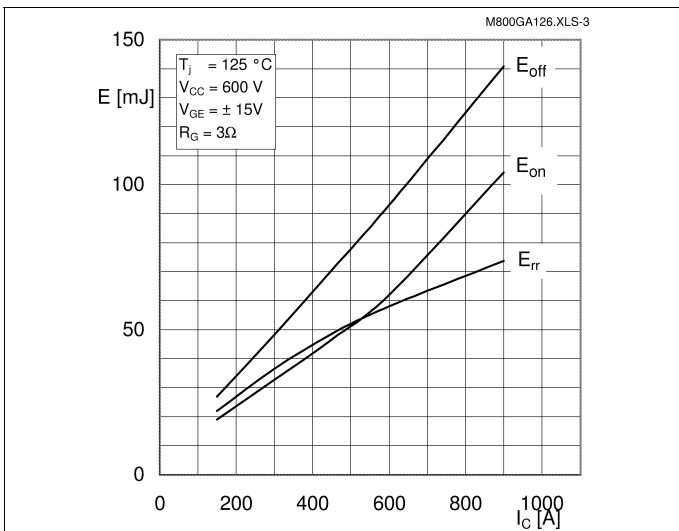


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

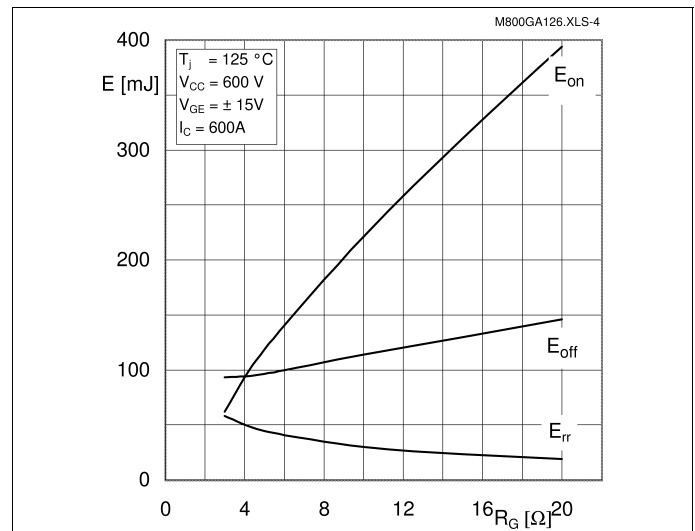


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

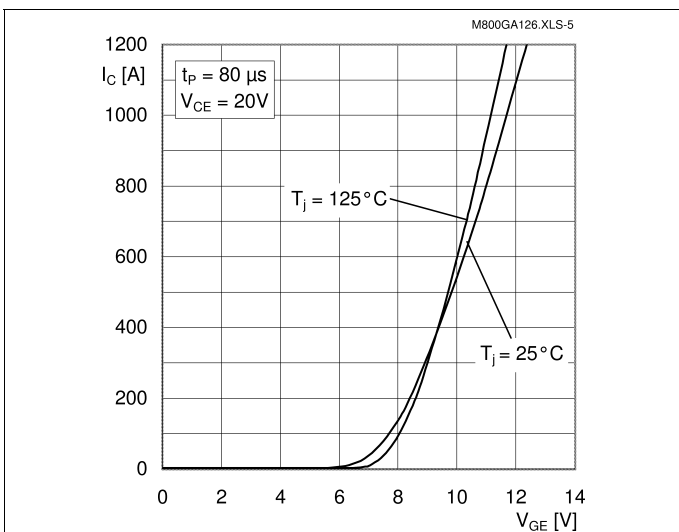


Fig. 5: Typ. transfer characteristic

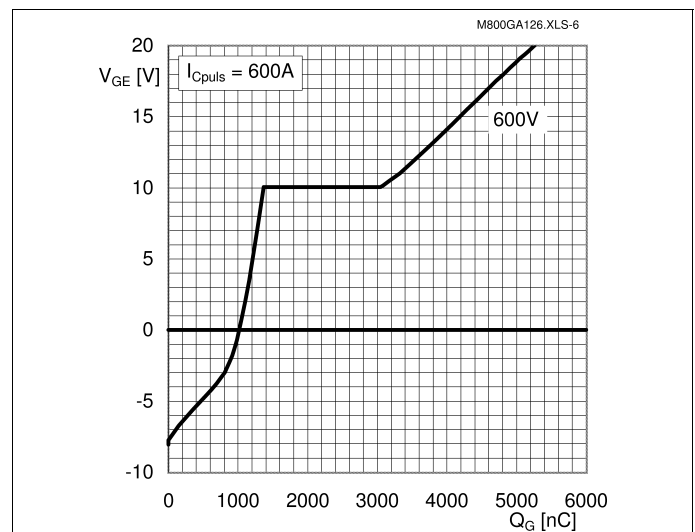


Fig. 6: Typ. gate charge characteristic

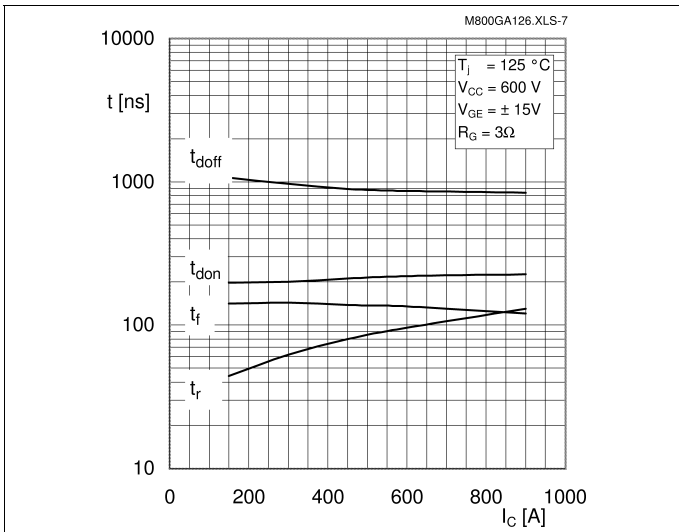


Fig. 7: Typ. switching times vs. I_C

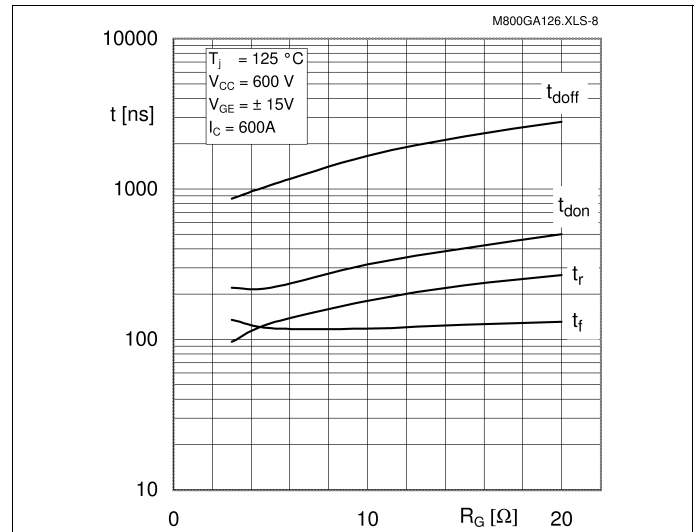


Fig. 8: Typ. switching times vs. gate resistor R_G

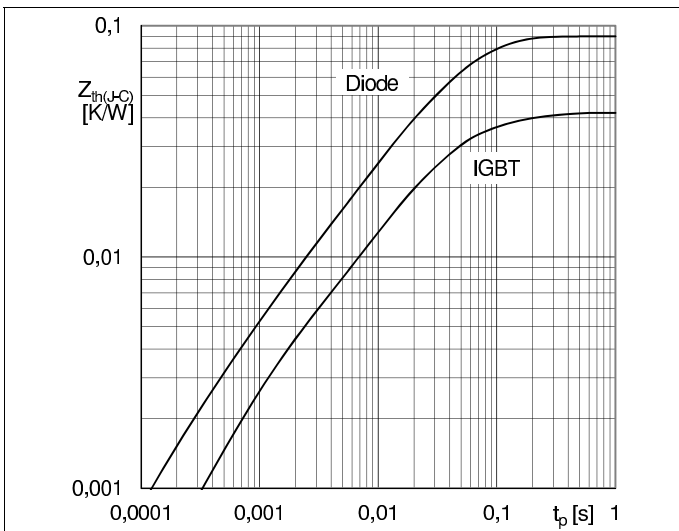


Fig. 9: Transient thermal impedance

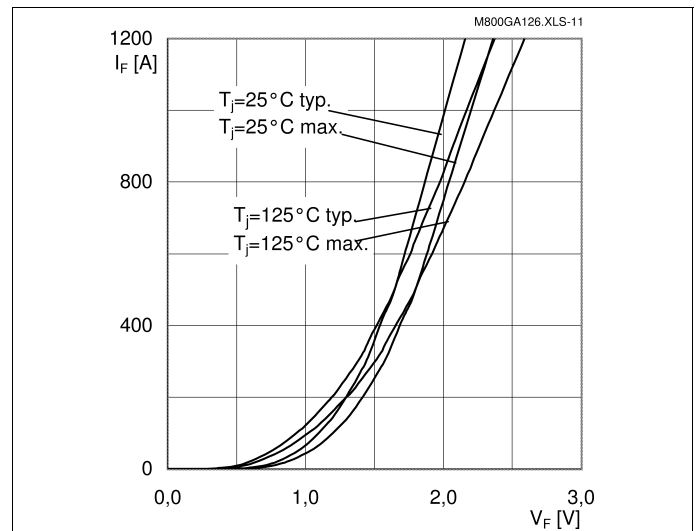


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC+EE'}$

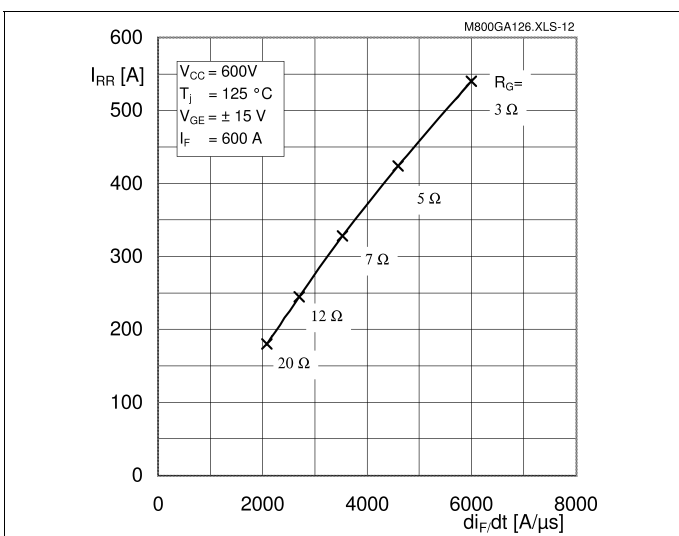


Fig. 11: Typ. CAL diode peak reverse recovery current

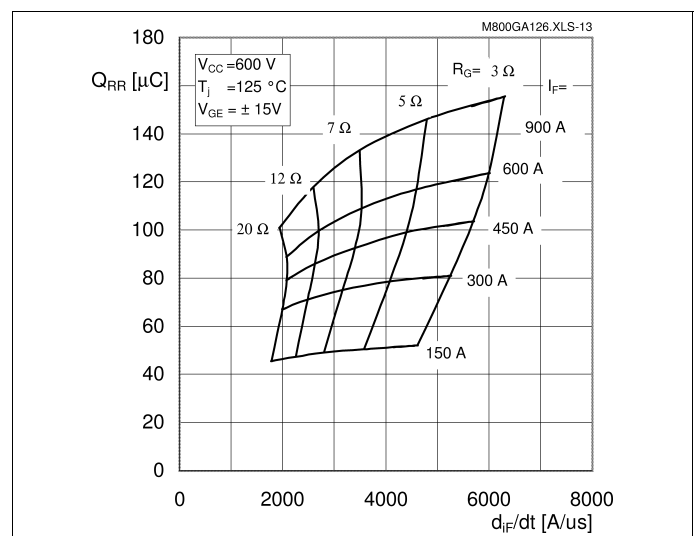
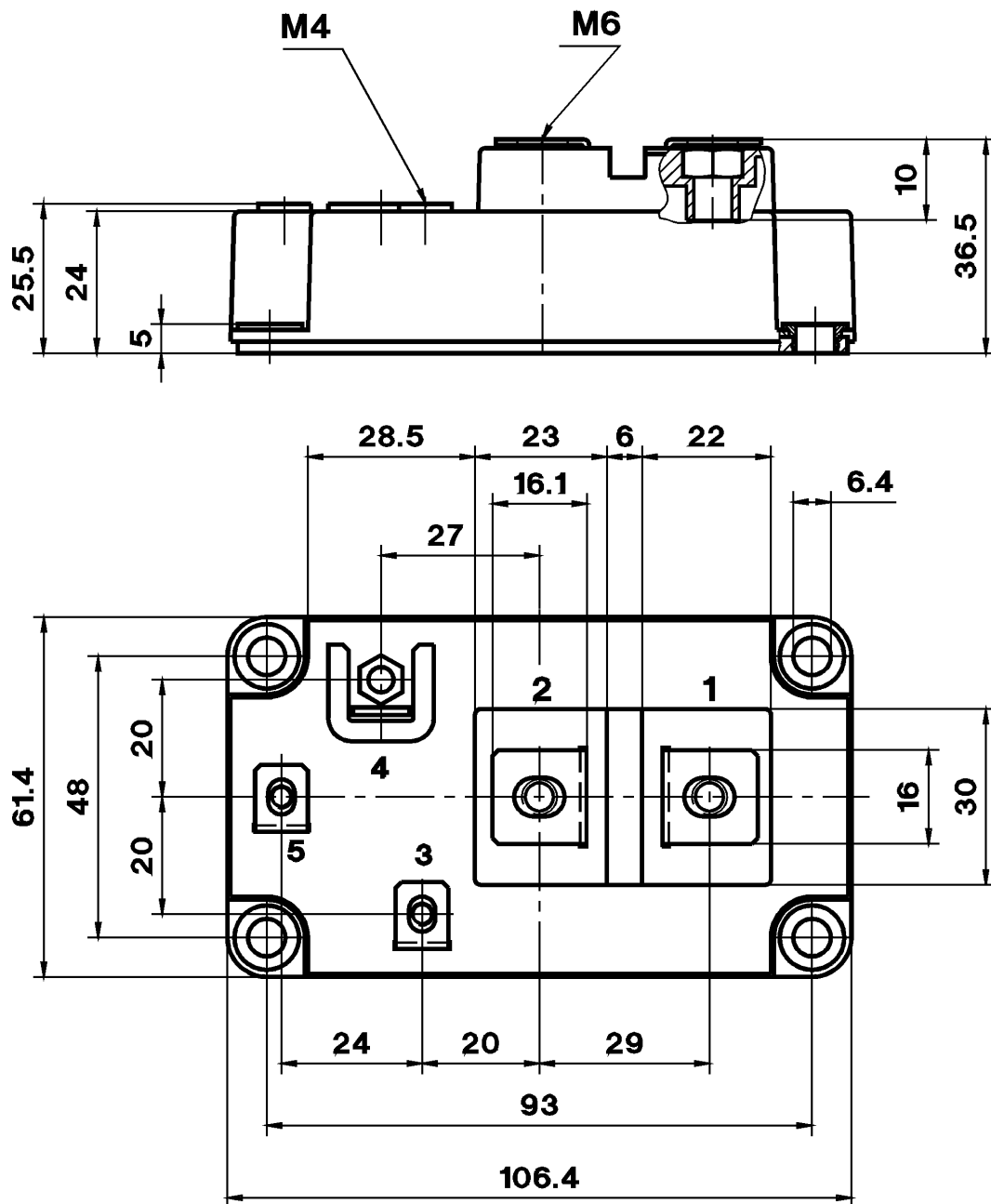
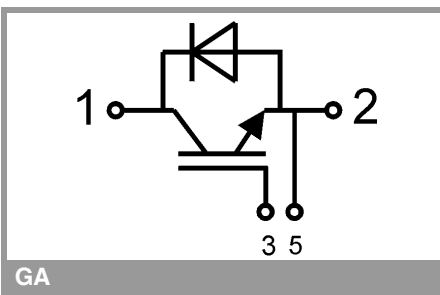


Fig. 12: Typ. CAL diode peak reverse recovery charge



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.